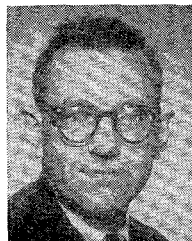


# Contributors

Aaron D. Bresler (S'43-A'46-M'55-SM'59) was born in New York, N. Y., on June 20, 1924. He received the B.E.E. degree from the City College of New York, N. Y., in 1944, and the M.E.E. and D.E.E. degrees, both from the Polytechnic Institute of Brooklyn, N. Y., in 1951 and 1959 respectively.



A. D. BRESLER

From 1944 to 1947 he served with the U. S. Army Signal Corps. In 1947 he worked as a telephone engineer for the United States forces in Austria. From 1948 to 1951, and again from 1953 to 1955, he was an instructor in the electrical engineering department of the City College of New York. In 1951 he joined the staff of the Microwave Research Institute at the Polytechnic Institute of Brooklyn, where he was engaged in development work on microwave components for two years. In 1955 he rejoined its staff and engaged in analytical studies of propagation and diffraction phenomena in anisotropic waveguides; these studies formed the basis upon which the D.E.E. degree was awarded to him. Recently, he joined the staff of Jasik Laboratories, Inc., Westbury, N. Y., where he has specialized in the design and development of antennas and microwave components.

Dr. Bresler is a member of Tau Beta Pi, Eta Kappa Nu and Sigma Xi.



John H. Craven (A'54) was born in Clacton, Essex, England on May 30, 1916. He received the B.S.E.E. degree from the University of British Columbia, Vancouver, in 1949 and the M.S. degree from the University of Toronto, Toronto, Ont., in 1950.



J. H. CRAVEN

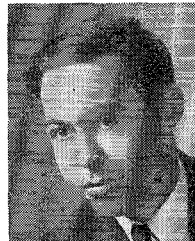
He served with the Royal Canadian Air Force from 1940 to 1945, having come to Canada in 1929. During 1950-1951 he worked at the Atomic Energy Project of the National Research Council at Chalk River, Ontario. Then he transferred to the Radio Division of the National Research Council in Ottawa, Ont., where he is presently employed. His work there has dealt with the development of a wide range of microwave devices.

Mr. Craven is an associate member of the British IRE.



Richard W. Damon was born on May 14, 1923, in Concord, Mass. He received the B.S. degree in physics in 1944 and the M.A.

and Ph.D. degrees in applied physics in 1947 and 1951, respectively, from Harvard University, Cambridge, Mass. From 1946 to 1948, and in 1950, he was a Teaching Fellow in Applied Physics at Harvard University.



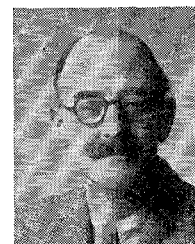
R. W. DAMON

During World War II, he was an electronics officer in the Naval Reserve, serving in underwater sound work at ship repair bases in Hawaii and the Philippine Islands. In 1948-49, he was employed as a magnetron development engineer at Raytheon Manufacturing Company, Waltham, Mass. He joined the General Electric Research Laboratory, Schenectady, N. Y., in 1951. His work there has been primarily in solid-state physics and has included photoconductivity, television camera tubes for the visible and X-ray regions, and the principles and applications of magnetic resonance phenomena.

Dr. Damon is a member of the American Physical Society, Sigma Xi, and the American Association for the Advancement of Science.



Charles Cecil Eaglesfield was born on June 28, 1906 in Swansea, Wales. He attended Clifton College, Clifton and received the M.A. degree from Petershouse, Cambridge in 1928.



C. C. EAGLESFIELD

He joined Standard Telephones and Cables, London, in 1928 where he assisted in the early days of the Transatlantic radio telephone service and the first ship-shore radio telephones. He joined Mullard Radio Valve Company, London, Eng., in 1933, and there worked on television until the war, when he initiated a number of valves used in radar. In 1947, he rejoined Standard Telephones to work on valves for repeaters and similar projects, and in 1957 he transferred to Standard Telecommunication Laboratories, Harlow, Essex, Eng., where he is presently employed. At STL, he has been associated with a project for long-distance communication by waveguide.

Mr. Eaglesfield is an Associate Member of the Institution of Electrical Engineers.



John R. Eshbach (S'47-A'51-M'57) was born on October 7, 1922, in Bethlehem, Pa. He received the B.S. degree in electrical en-

gineering and M.S. degree in physics from Northwestern University, Evanston, Ill., in 1946 and 1947 respectively. From 1943 to 1946 he served in the U. S. Navy. In 1951 he received the Ph.D. degree from the Massachusetts Institute of Technology, Cambridge, where he had done research in the field of microwave spectroscopy.



J. R. ESHBACH

Since 1951 he has been with the General Electric Research Laboratory in Schenectady, N. Y., where he has done research on photoconductivity and has worked on television camera tube principles and the development of camera tubes. Recently he has become engaged in research on ferromagnetic resonance and the principles of ferrite devices.

Dr. Eshbach is a member of the American Physical Society, Eta Kappa Nu, Tau Beta Pi and Sigma Xi.



Robert V. Garver (A'57) was born on June 2, 1932, in Minneapolis, Minn. He attended the University of Maryland, College Park, where he was awarded the Bachelor of Science degree in physics in 1956.



R. V. GARVER

In 1956 he became affiliated with the Microwave Development Section of Diamond Ordnance Fuze Laboratories, Washington, D. C., where he has been working on microwave semiconductors.

Mr. Garver is a member of the American Physical Society.



Jerome J. Green was born in Chicago, Ill., on October 10, 1932. He received the B.S. degree in physics from Northwestern University, Evanston, Ill., in 1954 and the M.A. and Ph.D. degrees from Harvard University, Cambridge, Mass., in 1955 and 1959, respectively.



J. J. GREEN

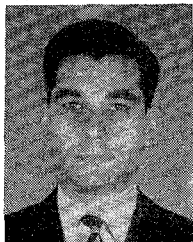
Dr. Green is presently employed at the Research Division, Raytheon Manufacturing Company, Waltham, Mass., where he is engaged in experimental studies of ferromagnetic resonance.

Jôji Hamasaki, for a photograph and biography please see page 397 of the July, 1959 issue of these TRANSACTIONS.

A. F. Harvey, for a photograph and biography please see page 482 of the October, 1959 issue of these TRANSACTIONS.

Kaneyuki Kurokawa, for a photograph and biography please see page 397 of the July, 1959 issue of these TRANSACTIONS.

Arthur A. Oliner (M'47-SM'52) was born in Shanghai, China, on March 5, 1921. He received the B.A. degree from Brooklyn College, N. Y., in 1941,



A. A. OLINER

and the Ph.D. degree in physics from Cornell University, Ithaca, N. Y., in 1946. While at Cornell, he held a graduate teaching assistantship in the physics department and also conducted research on an Office of Scientific Research and Development project.

Since 1946, he has been with the Microwave Research Institute of the Polytechnic Institute of Brooklyn, N. Y., where he has been engaged in research in a variety of topics in the microwave field. He has also taught graduate courses in physics and electrical engineering, and is a research professor.

Dr. Oliner is Chairman of both the IRE Committee on Antennas and Waveguides and the IRE Professional Group on Microwave and Theory and Techniques. He is a member of Commissions 1 and 6.3 of URSI, the American Physical Society and Sigma Xi. He is also on the National Academy of Sciences Advisory Panel to the National Bureau of Standards.

John A. Rosado was born on June 15, 1936, in Baton Rouge, Louisiana. In 1958 he received the degree of Bachelor of Arts in physics from Harvard University, Cambridge, Mass.



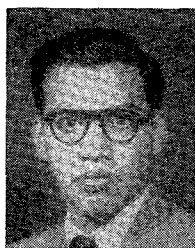
J. A. ROSADO

Upon graduation from Harvard, Mr. Rosado was employed by the Ordnance Corps, Diamond Ordnance Fuze Laboratories, Washington 25, D. C.

Raman Lal Sarda was born on February 25, 1933 in Jaisalmer, India. He received the B.E. degree in telecommunications engineer-

ing from Government Engineering College, Jabalpur, India, in 1955.

After some short assignments, he joined the research staff of the newly started Central Electronics Engineering Research Institute, Pilani, in 1956.



R. L. SARDA

He worked there for some time on research projects, "Radar Detecting System" and "Linearity of Cavity Resonators." In 1958, he came to the United States for graduate studies on a scholarship from Mahindra Educational Trust, Bombay. He is currently finishing work for the M.S. degree in electrical engineering at Stanford University, Stanford, Calif.

Joseph H. Saunders was born on January 18, 1919, in Freeport, Nova Scotia. He graduated from Wentworth Institute, Boston, Mass., in 1940, and did subsequent graduate study at Northeastern University in Boston.



J. H. SAUNDERS

From 1941 to 1947 he was employed by the Holtzer-Cabot Electric Company and the Faraday Electric Company as an engineer on protective signal systems. In 1947, he joined the Raytheon Company, Waltham, Mass. where his work has been mostly in the microwave field. At present he is engaged in the study of the microwave properties and applications of ferrites.

Ernst Schlömann was born in Borgholzhausen, Germany on December 13, 1926. He received the M.S. degree in 1953 and the Ph.D. degree in 1954 in theoretical physics from the University of Göttingen, Göttingen, Germany. In 1954-1955 he did postdoctoral research at the Massachusetts Institute of Technology, Cambridge, Mass., in theoretical solid state physics.

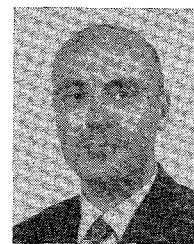


E. SCHLÖMANN

He was employed at the Research Division, Raytheon Manufacturing Company, Waltham, Mass., from 1954-1955 on a part time basis. He joined Raytheon on a full time basis in August 1955, and is currently engaged in theoretical studies of ferromagnetism, particularly ferromagnetic resonance.

Dr. Schlömann is a member of the American Physical Society.

Jean-Claude Simon (SM'53) was born September 10, 1923, in Paris, France. He graduated from the École Polytechnique in 1944 and received the D.Sc. degree in mathematics and physics from the Sorbonne in 1952. In the summer of 1948 he was a member of the Foreign Summer Student Project at M.I.T., Cambridge, Mass.



J. C. SIMON

From 1947 to 1949 he was with the French Navy at the laboratory of ENS, Paris. In 1949 he became a physicist at the Compagnie Générale de Télégraphie sans Fil, Paris. In 1951 he was appointed head of the laboratory at CSF, and in 1957 he became technical director of the Applied Physics Department.

Dr. Simon has published 21 articles and papers, and he holds 30 French or foreign patents. He became a Lauréat de l'Institut in 1952, the Ferrié Prize of the Society of Radioelectricians in 1953 and the Blondel Medal in 1959. He is a member of the French Society of Physics, the French Society of Radioelectricians, and the French Society of Statistics.

Marshall H. Sirvetz was born in Lynn, Mass., in 1924. In 1950 he received the Ph.D. degree in chemical physics from Harvard University, Cambridge, Mass., where he did work in microwave spectroscopy.



M. H. SIRVETZ

After spending two years at Brookhaven National Laboratory, Long Island, N. Y., he joined the Research Division of Raytheon Manufacturing Company, Waltham, Mass., in March, 1953, where he is presently employed. His present work deals with the microwave properties and applications of ferrites and with solid-state microwave amplifiers.

L. Solymar was born on January 24, 1930, in Budapest, Hungary. In 1952 he received the diploma of Electrical Engineer from the Technical University of Budapest, where he was assistant to the professor from 1952 to 1953.



L. SOLYMAR

From 1953 to 1956, he was a research engineer at the Research Institute of Telecommunication, Budapest, and was engaged in antenna theory

and design. In 1956 he became a research engineer at the Standard Telecommunication Laboratories Ltd., Harlow, Essex, Eng., where he is presently employed and where he has been concerned with various topics in microwave transmission.



Allan Staniforth (A'45-M'55-SM'58) was born in Alberta, Can., on October 9, 1915. He received the B.A.Sc. degree at the University of British Columbia, Vancouver, in 1938.



A. STANIFORTH  
He worked for the Canadian Broadcasting Corporation for three and one-half years as transmitter supervisor. Since that time, he has been with the Radio and Electrical Engineering Division of the National Research Council, Ottawa, Canada.



Edward F. Turner, Jr. was born on April 21, 1920, in Newport News, Va. He received the B.S. degree in physics and the B.A. degree in mathematics from Washington and Lee University, Lexington, Va., in 1950. Upon completion of the M.S. degree from the Massachusetts Institute of Technology, Cambridge, Mass., in 1952 and

the Ph.D. from the University of Virginia, Charlottesville, Va., in 1954, he taught for three years at George Washington University, Washington, D. C. He has spent his summers doing research at the Naval Research Laboratory and the Diamond Ordnance Fuze Laboratory in Washington, D. C., principally in the fields of High Resistance Measurements and Semiconductor Switching of Micro-



E. F. TURNER

waves. At present he is Professor of Physics at Washington and Lee University.

Dr. Turner is a member of Phi Beta Kappa, Sigma Xi, and Sigma Pi Sigma.



B. H. Wadia (S'50-A'53) was born on October 1, 1927, in Surat, India. He received the B.E. degree in electrical and mechanical engineering, in 1948, from the University of Bombay, Bombay, India. He received the M.S. degree in 1950 and the Ph.D. degree in 1954, both in electrical engineering from Stanford University, Stanford, Calif. While at Stanford, he was a research assistant, and subsequently a research associate in the Electronics Research Laboratories.



B. H. WADIA

After his academic work, he joined the engineering staff of Machlett Laboratories,

Inc., Springdale, Conn., and was given the position of Product Engineer (UHF Tubes). At the end of 1956, he returned to India and was made assistant director in charge of the Central Electronics Engineering Research Institute, Pilani, Rajasthan, India. He was instrumental in setting up one of the first organizations devoted exclusively to electronic engineering, research and development work in that country. At present he holds a teaching position in the Department of Electrical Engineering at the newly organized Indian Institute of Higher Technology, Bombay, India.

Dr. Wadia is a member of Tau Beta Pi and Sigma Xi.



Ernest J. Wilkinson (S'52-A'53) was born in Fall River, Mass. on May 23, 1927. He received the B.S. degree in electrical engineering from Northeastern University, Boston, Mass., in 1952 and the M.S. degree in electrical engineering from Stanford University, Stanford, Calif. in 1956.



E. J. WILKINSON

From 1952 to 1953 he was employed by Sandia Corporation, Albuquerque, N. M., and from 1953 to 1954 he worked for Sylvania Electric Products, Inc., then located in Boston, Mass. He returned to Sylvania in 1956 and is presently working in the Electronics Department of the Missile Systems Laboratory located in Waltham, Mass.

Mr. Wilkinson is a member of Tau Beta Pi and Eta Kappa Nu.